

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A process for producing a silicon single crystal comprising

pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to a magnetic field consisting of a traveling magnetic field which exerts a substantially vertically downward oriented force on the melt in a region of the crucible wall and

applying the magnetic field with an intensity which is sufficient to attenuate low-frequency temperature fluctuations in the melt and to establish a convection which is initially directed to a bottom of the crucible.

2. (Original) The process as claimed in claim 1,

wherein the silicon single crystal is pulled with an oxygen concentration of at least $5 * 10^{17}$ atoms per cm^3 .

3-13. (Canceled)

14. (Currently Amended) A process for producing a silicon single crystal, comprising

pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to a magnetic field consisting of a traveling magnetic field which exerts a substantially vertically downward oriented force on the melt in a region of the crucible wall;

applying the magnetic field with an intensity which is sufficient to attenuate low-frequency temperature fluctuations in the melt and to establish a convection which is initially directed to a bottom of the crucible; and

generating the magnetic field with three coils and connecting said three coils to a 3-phase power supply, with a phase angle in an order 0°-60°-120° or 0°-120°-240°.

15-16. (Canceled)

17. (currently amended) A process for producing a silicon single crystal, comprising

pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to a magnetic field consisting of a traveling magnetic field which exerts a substantially vertically upwardly upward oriented force on the melt in a region of the crucible wall, and

applying the magnetic field with an intensity which is sufficient to attenuate low-frequency temperature fluctuations in the melt.

18. (Canceled)